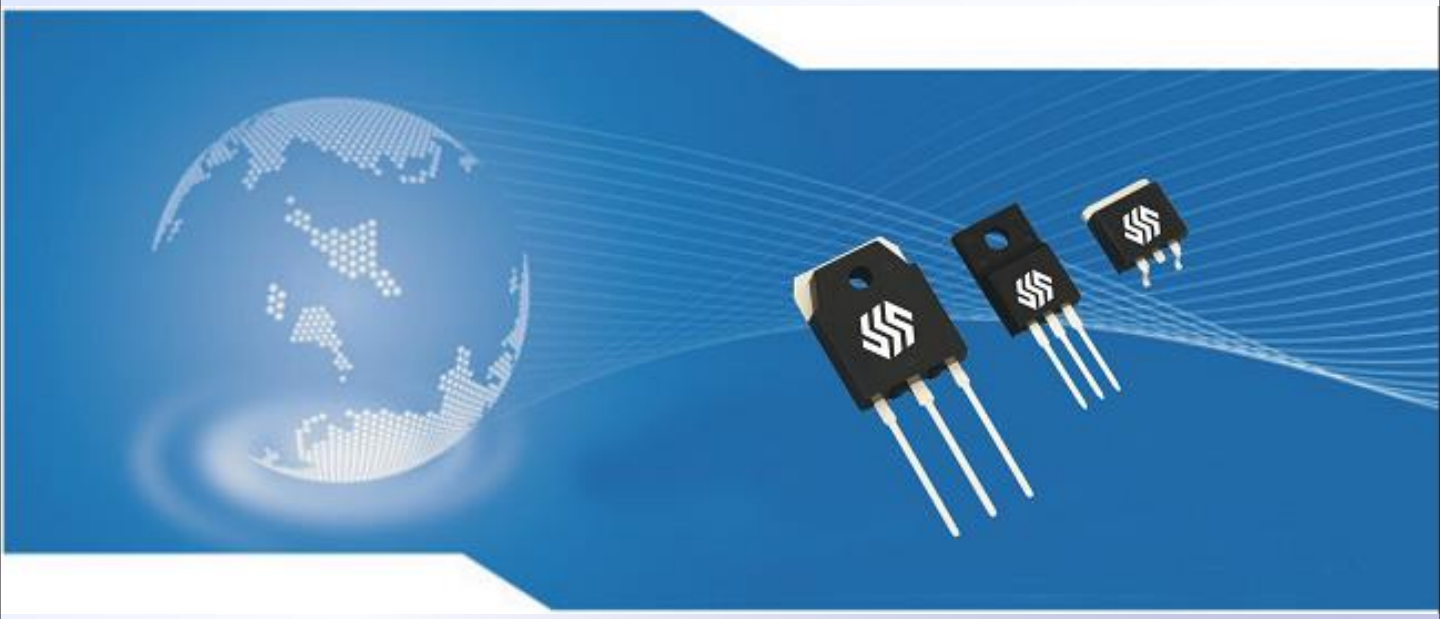
SUPER-SEMI



SUPER-MOSFET

Super Junction Metal Oxide Semiconductor Field Effect Transistor

500V Super Junction Power Transistor
SS*50R240S

Rev. 1.2
May. 2018

www.supersemi.com.cn

SSF50R240S/SSP50R240S/SSW50R240S/SSA50R240S
500V N-Channel MOSFET

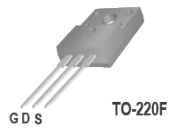
Description

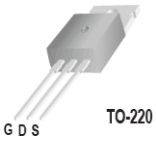
SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.
This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy.
SJ-FET is suitable for various AC/DC power conversion in switching mode operation for higher efficiency.

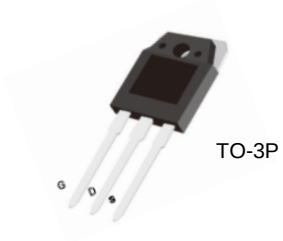
Features

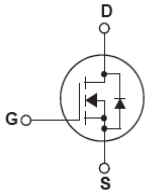
- Multi-Epi process SJ-FET
- 550V @TJ = 150 ℃
- Typ. RDS(on) = 0.21Ω
- Ultra Low Gate Charge (typ. Qg = 21nC)
- 100% avalanche tested

SSF50R240S SSP50R240S SSW50R240S SSA50R240S









Absolute Maximum Ratings

Symbol	Parameter	SSP_W_A50R240S	SSF50R240S	Unit
V_{DSS}	Drain-Source Voltage	500		V
I_D	Drain Current -Continuous (TC = 25℃) -Continuous (TC = 100℃)	18* 11*		A
I_{DM}	Drain Current - Pulsed (Note 1)	55*		A
V_{GSS}	Gate-Source voltage	±30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	284		mJ
I_{AR}	Avalanche Current (Note 1)	2.4		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	0.43		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	15		V/ns
dVds/dt	Drain Source voltage slope (Vds=400V)	50		V/ns
P_D	Power Dissipation (TC = 25℃)	104	34	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		℃
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300		℃

* Drain current limited by maximum junction temperature. Maximum duty cycle D=0.75.

Thermal Characteristics

Symbol	Parameter	SSP_W_A50R240S	SSF50R240S	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.2	3.9	℃/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	80	℃/W

Electrical Characteristics TC = 25℃ unless otherwise noted

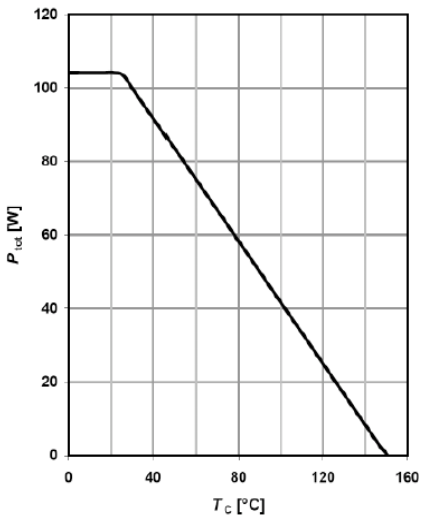
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA, T_J = 25℃	500	-	-	V
		V_{GS} = 0V, I_D = 250μA, T_J = 150℃	-	550	-	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25℃	-	0.6	-	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 500V, V_{GS} = 0V -T_J = 150℃	-	- 10	1 -	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	-	-	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	-	-	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 9A	-	0.21	0.24	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40V, I_D = 18A	-	12	-	S
Rg	Gate resistance	f=1 MHz, open drain	-	3.5	-	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz	-	800	-	pF
C_{oss}	Output Capacitance		-	340	-	pF
C_{rss}	Reverse Transfer Capacitance		-	10	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400V, I_D = 9A R_G = 20Ω(Note 4)	-	13	-	ns
t_r	Turn-On Rise Time		-	11	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	100	-	ns
t_f	Turn-Off Fall Time		-	12	-	ns
Q_g	Total Gate Charge	V_{DS} = 400V, I_D = 9A V_{GS} = 10V (Note 4)	-	21	-	nC
Q_{gs}	Gate-Source Charge		-	5	-	nC
Q_{gd}	Gate-Drain Charge		-	7.7	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		-	-	18	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		-	-	55	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_S = 9A	-	0.9	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_S = 9A dI_F/dt =100A/μs	-	345	-	ns
Q_{rr}	Reverse Recovery Charge		-	4.5	-	μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS}=2.4A, VDD=50V, Starting TJ=25 ℃
3. I_{SD}≤ID, di/dt ≤ 200A/us, V_{DD} ≤ BV_{DSS}, Starting TJ = 25 ℃
4. Essentially Independent of Operating Temperature Typical Characteristics

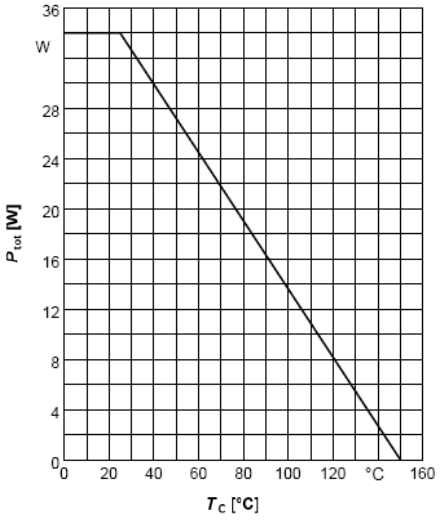
Typical Performance Characteristics

Power dissipation
TO-220, TO-247, TO-262, TO-263



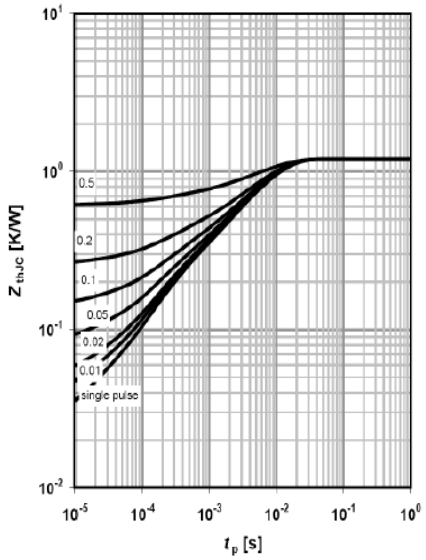
$P_{tot} = f(T_C)$

Power dissipation
TO-220 FullPAK



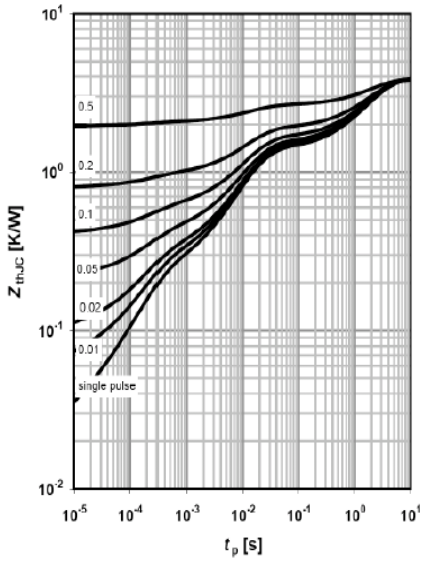
$P_{tot} = f(T_C)$

Max. transient thermal impedance
TO-220, TO-247, TO-262, TO-263



$Z_{(thJC)}$=f(tp); parameter: D=t_p/T

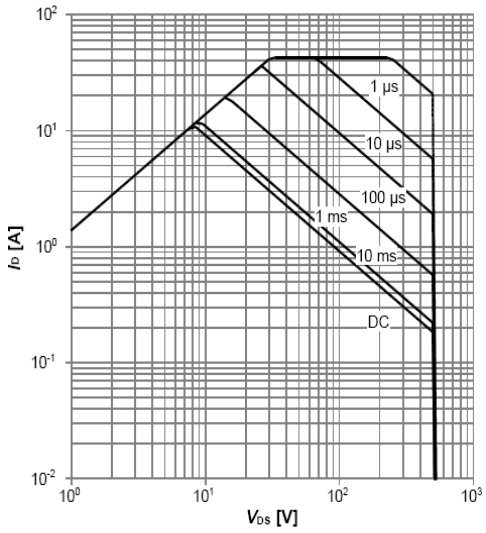
Max. transient thermal impedance
TO-220 FullPAK



$Z_{(thJC)}$=f(tp); parameter: D=t_p/T

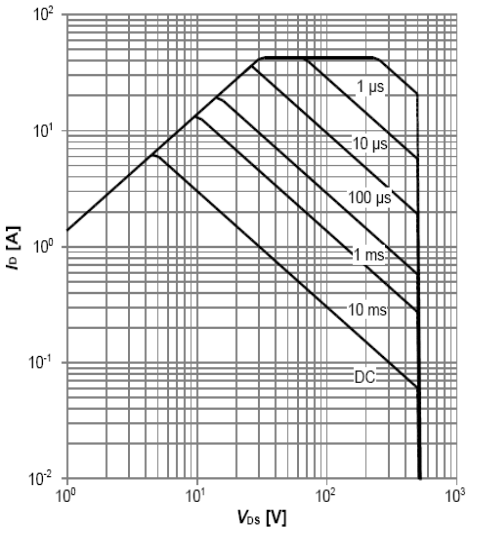
Typical Performance Characteristics

Safe operating area T_C=25 °C
TO-220, TO-247, TO-262, TO-263



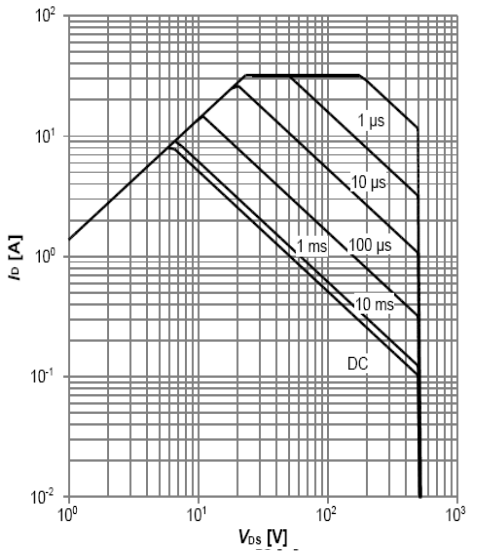
I_D=f(V_{DS}); T_C=25 °C; D=0; parameter t_p

Safe operating area T_C=25 °C
TO-220 FullPAK



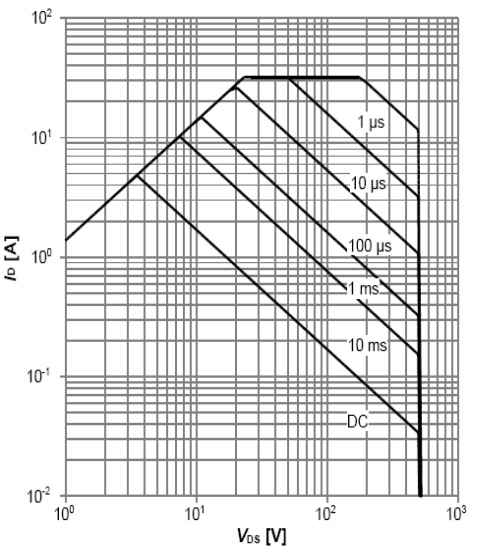
I_D=f(V_{DS}); T_C=25 °C; D=0; parameter t_p

Safe operating area T_C=80 °C
TO-220, TO-247, TO-262, TO-263



I_D=f(V_{DS}); T_C=80 °C; D=0; parameter t_p

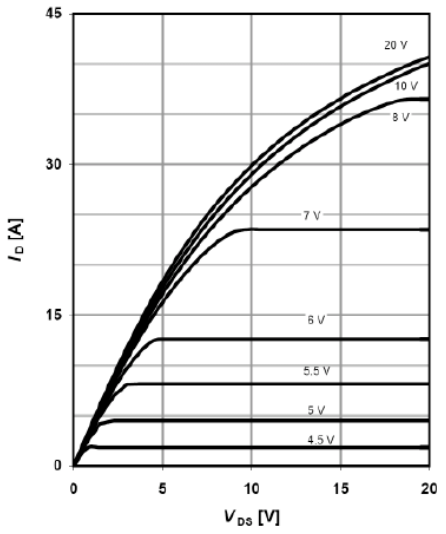
Safe operating area T_C=80 °C
TO-220 FullPAK



I_D=f(V_{DS}); T_C=80 °C; D=0; parameter t_p

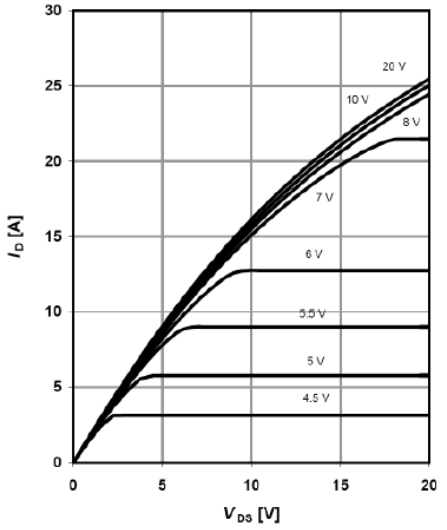
Typical Performance Characteristics

Typ. output characteristics T_j=25 °C



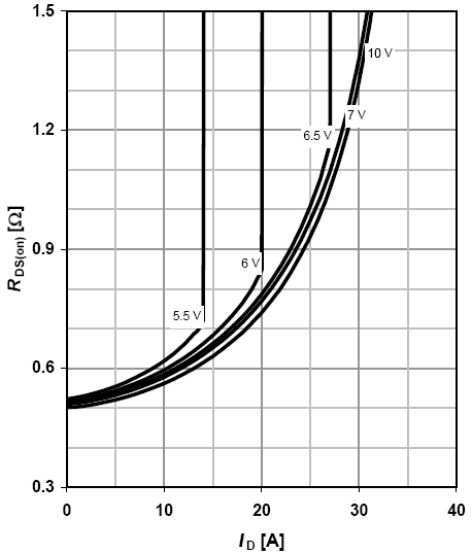
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}

Typ. output characteristics T_j=125 °C



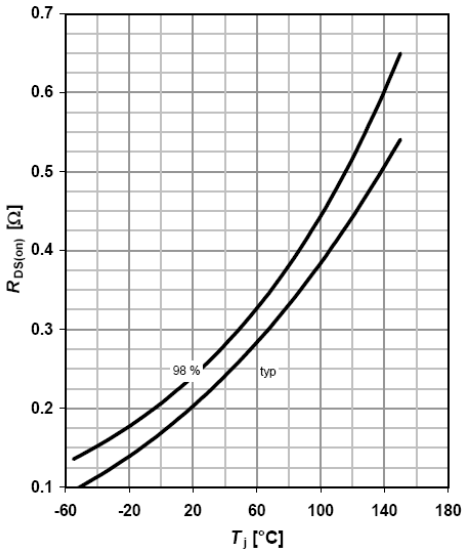
I_D=f(V_{DS}); T_j=125 °C; parameter: V_{GS}

Typ. drain-source on-state resistance



$R_{DS(on)}$=f(I_D); T_j=125 °C; parameter: V_{GS}

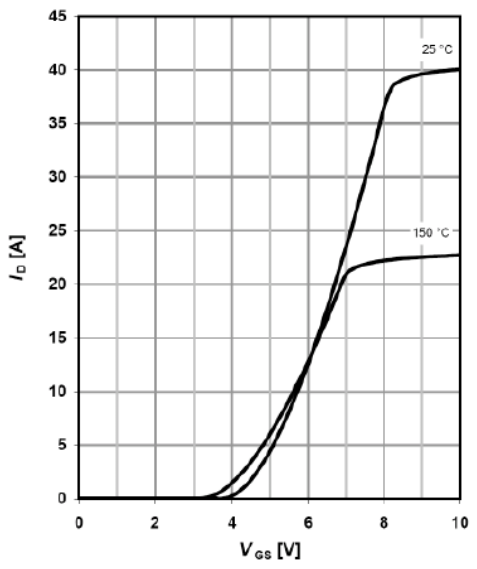
Drain-source on-state resistance



$R_{DS(on)}$=f(T_j); I_D=6.5 A; V_{GS}=10 V

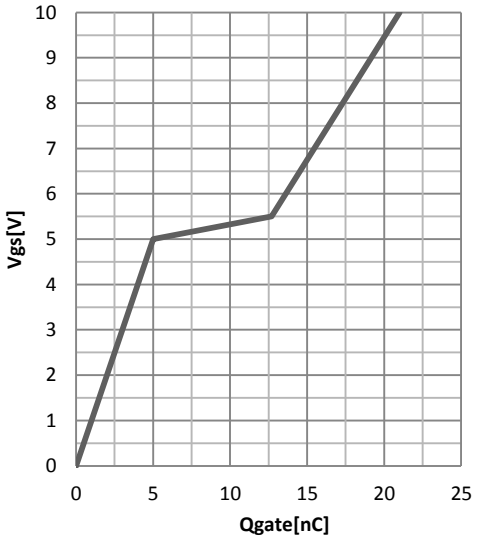
Typical Performance Characteristics

Typ. transfer characteristics



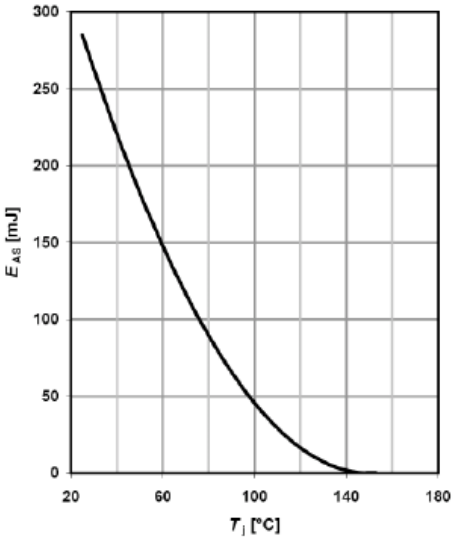
$I_D=f(V_{GS})$; $V_{DS}=20V$

Typ. gate charge



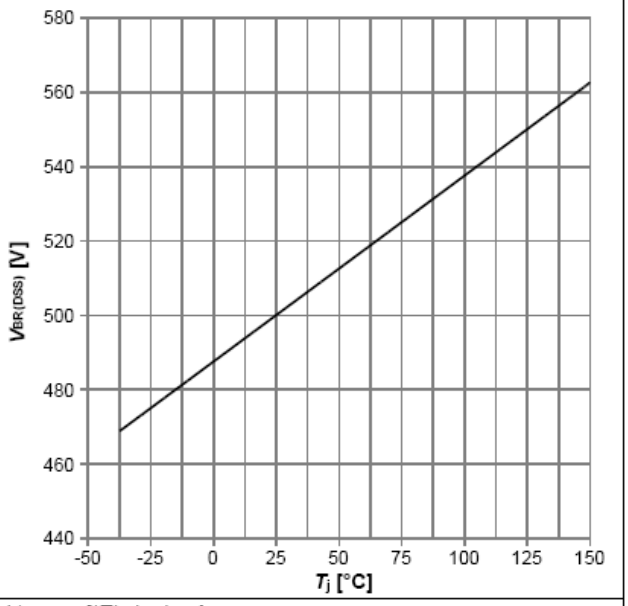
$V_{GS}=f(Q_{gate})$, $I_D=6.5A$ pulsed

Avalanche energy



$E_{AS}=f(T_j)$; $I_D=2.4$ A; $V_{DD}=50$ V

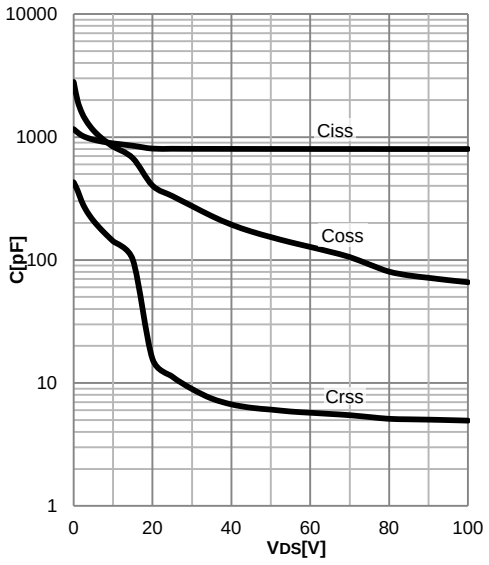
Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$; $I_D=1$ mA

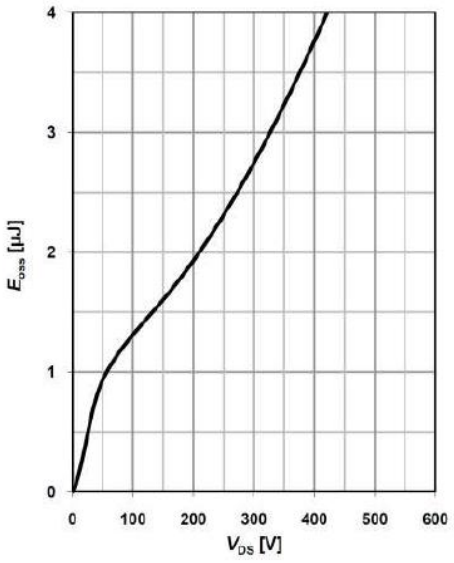
Typical Performance Characteristics

Typ. capacitances



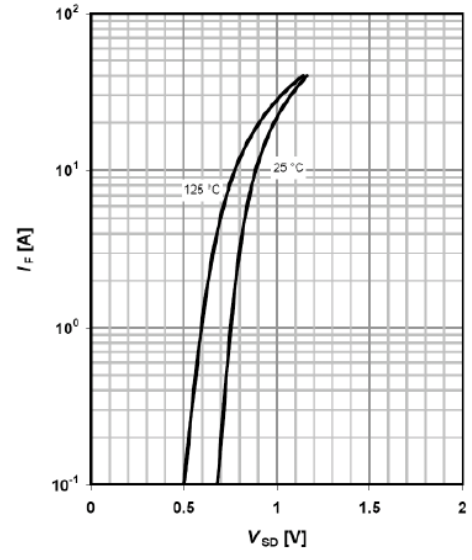
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Typ. C_{oss} stored energy



E_{oss}=f(V_{DS})

Forward characteristics of reverse diode

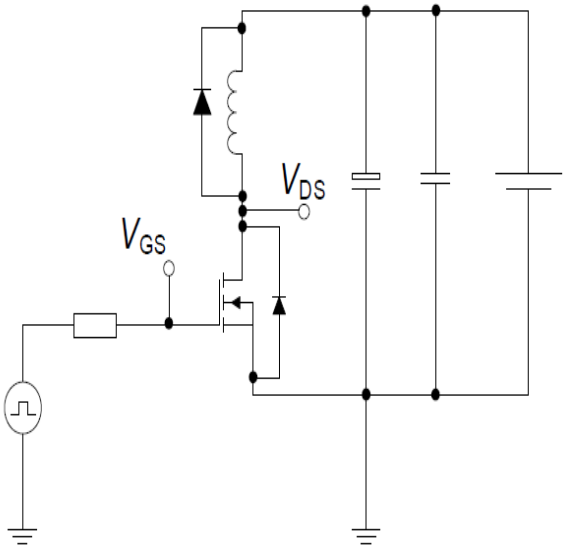


I_F=f(V_{SD}); parameter: T_j

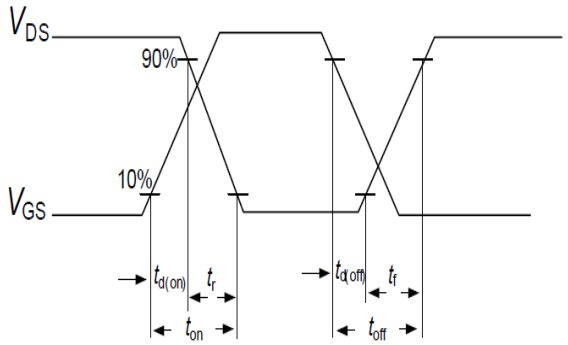
Test circuits

Switching times test circuit and waveform for inductive load

Switching times test circuit for inductive load

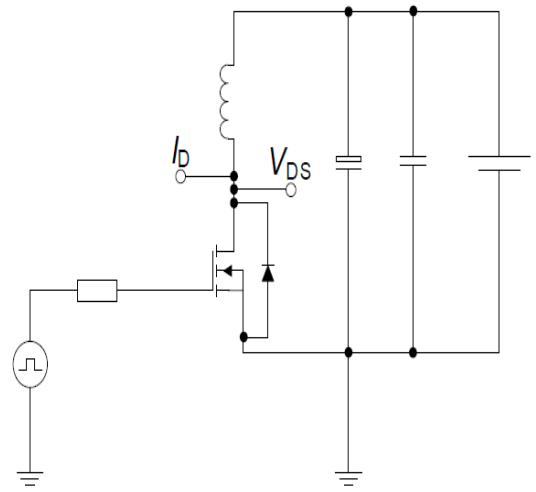


Switching time waveform

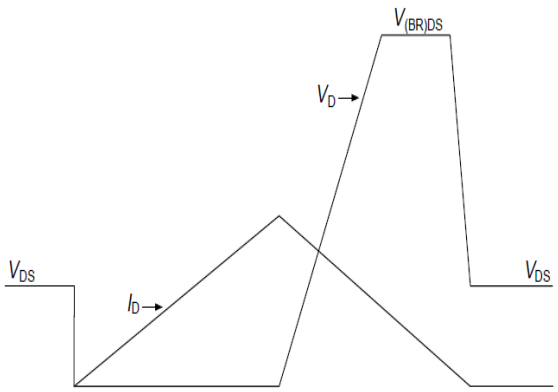


Unclamped inductive load test circuit and waveform

Unclamped inductive load test circuit



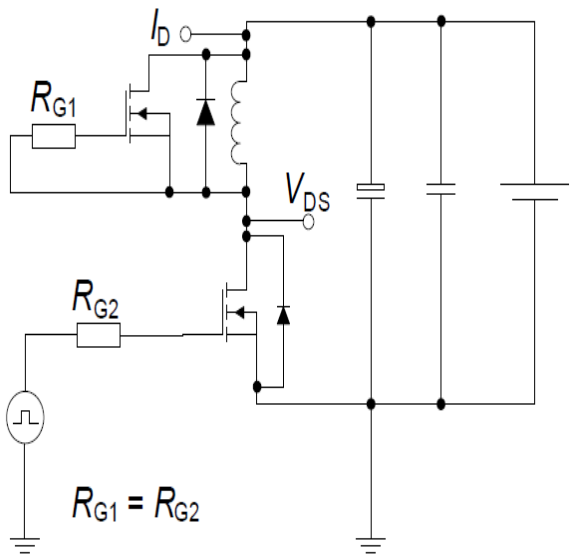
Unclamped inductive waveform



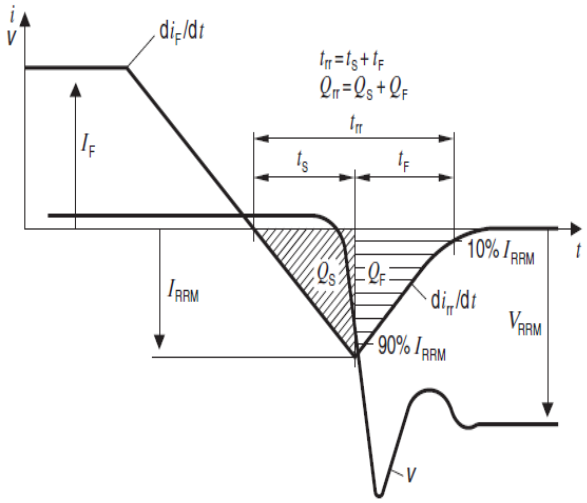
Test circuits

Test circuit and waveform for diode characteristics

Test circuit for diode characteristics

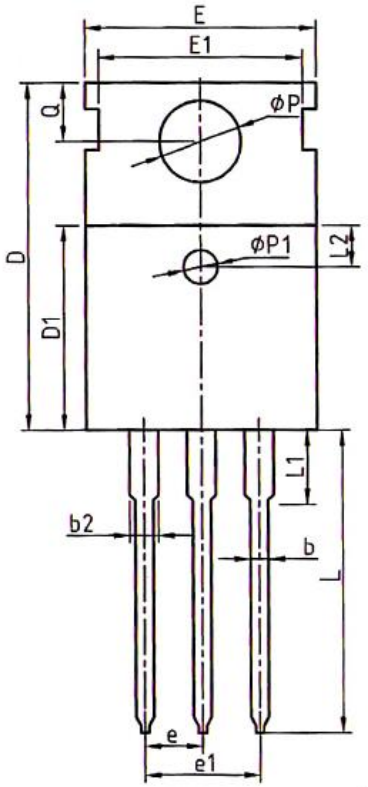


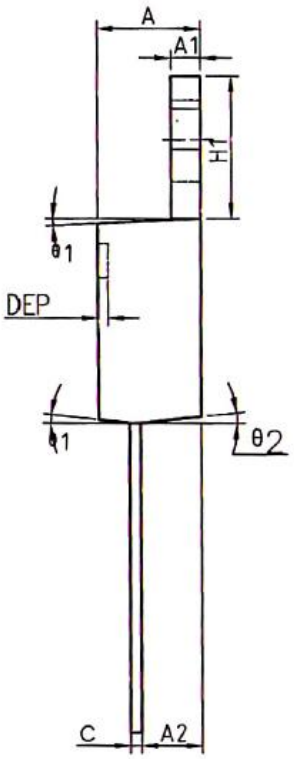
Diode recovery waveform

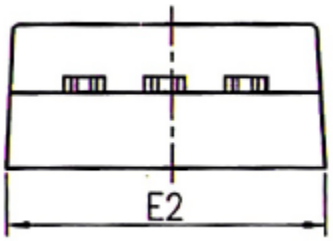


Package Outline

TO-220





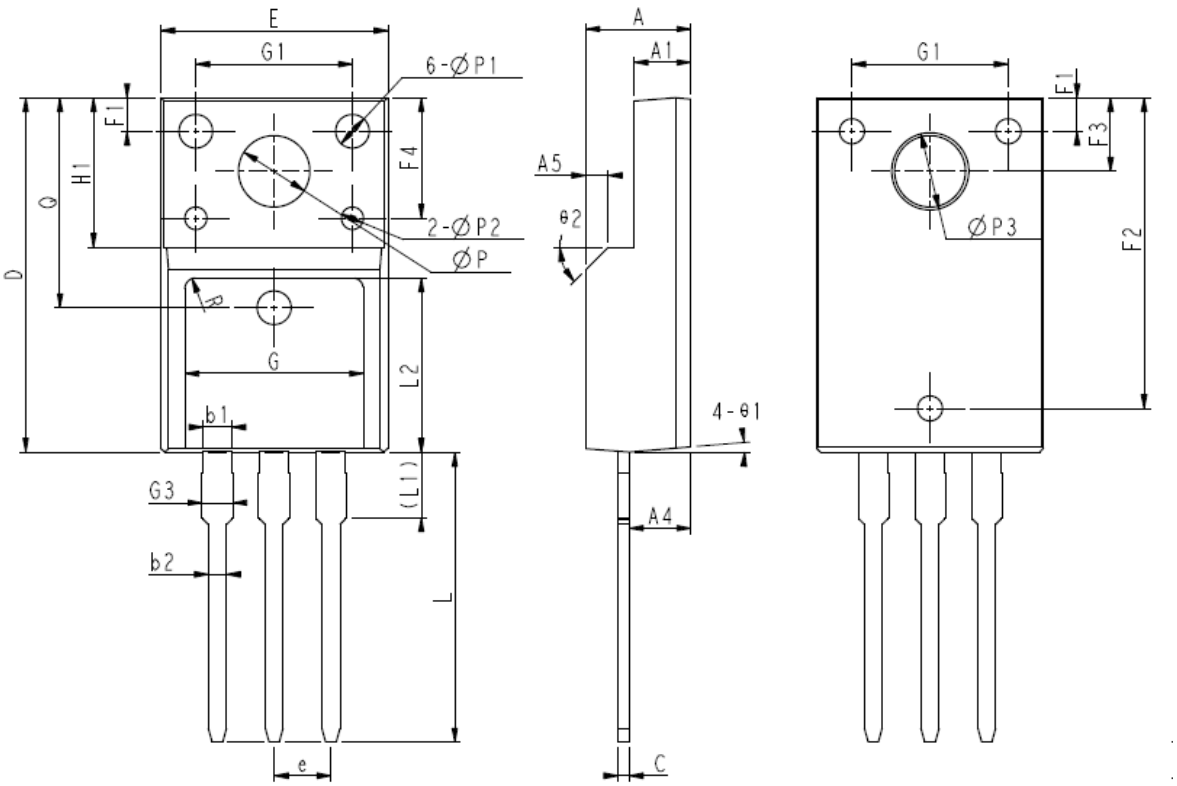


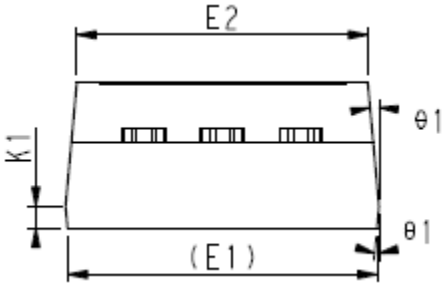
COMMON DIMENIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.40	4.57	4.70
A1	1.27	1.30	1.37
A2	2.35	2.40	2.50
b	0.77	0.80	0.90
b2	1.17	1.27	1.36
c	0.48	0.50	0.56
D	15.40	15.60	15.80
D1	9.00	9.10	9.20
DEP	0.05	0.10	0.20
E	9.80	10.00	10.20
E1	–	8.70	–
E2	9.80	10.00	10.20
ΦP1	1.40	1.50	1.60
e	2.54BSC		
e1	5.08BSC		
H1	6.40	6.50	6.60
L	12.75	13.50	13.65
L1	–	3.10	3.30
L2		2.50REF	
ΦP	3.50	3.60	3.63
Q	2.73	2.80	2.87
θ1	5°	7°	9°
θ2	1°	3°	5°
θ3	1°	3°	5°

Package Outline

TO-220 Full PAK



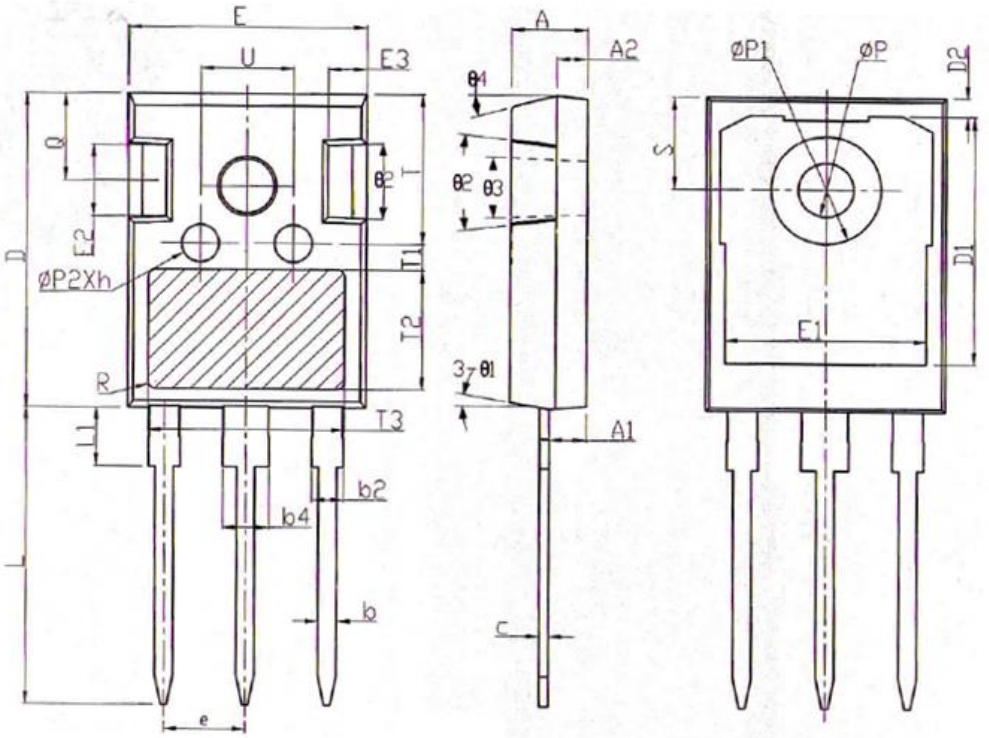


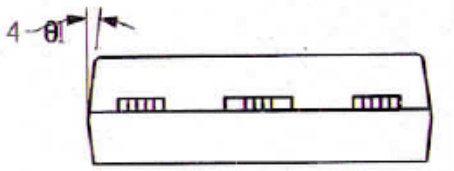
COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
E	10.00	10.16	10.32
E1	9.94	10.04	10.14
E2	9.36	9.46	9.56
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A4	2.66	2.76	2.86
A5		1.00REF	
c	0.45	0.50	0.60
D	15.67	15.87	16.07
Q		9.40REF	
H1		6.70REF	
e		2.54BSC	
ΦP		3.18REF	
L	12.78	12.98	13.18
L1	2.83	2.93	3.03
L2	7.70	7.80	7.90
ΦP1	1.40	1.50	1.60
ΦP2	0.95	1.00	1.05
ΦP3		3.45REF	
θ1	3°	5°	7°
θ2	-	45°	-
F1	1.00	1.50	2.00
F2	13.80	13.90	14.00
F3	3.20	3.30	3.40
F4	5.30	5.40	5.50
G	7.80	8.00	8.20
G1	6.90	7.00	7.10
G3	1.25	1.35	1.45
b1	1.23	1.28	1.38
b2	0.75	0.80	0.90
K1	0.65	0.70	0.75
R		0.50REF	

Package Outline

TO-247



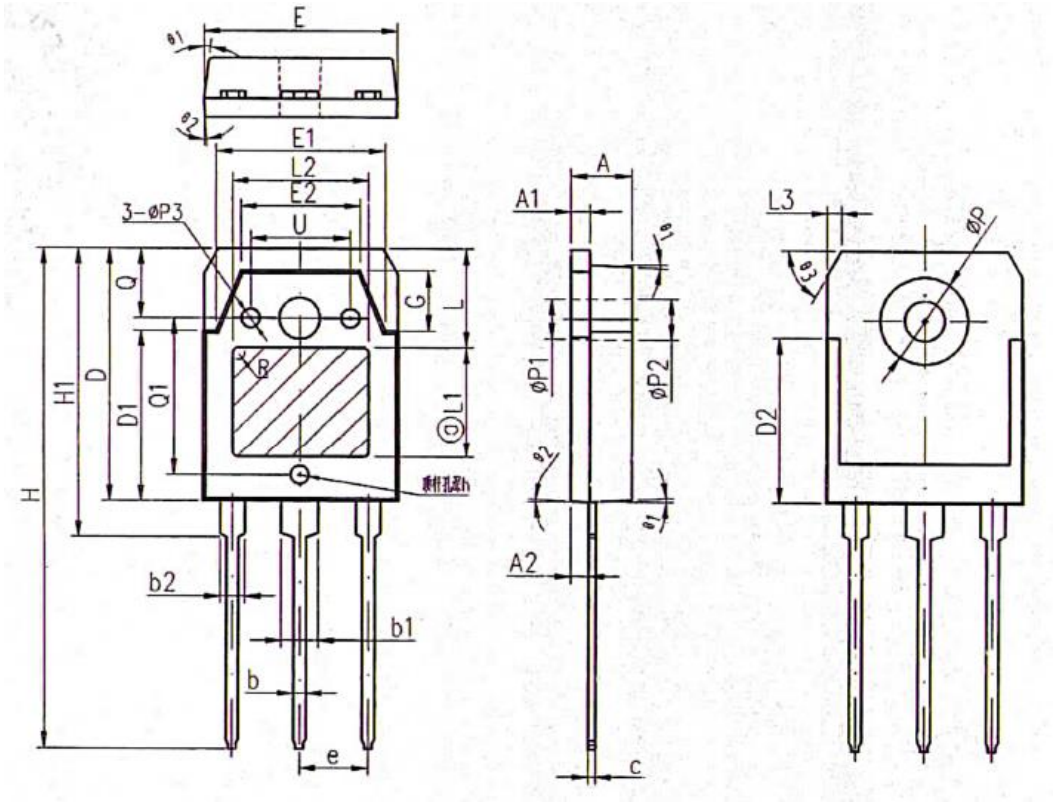


COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16	1.21	1.26
b2	1.96	2.01	2.06
b4	2.96	3.01	3.06
c	0.59	0.61	0.66
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e		5.44BSC	
h	0.05	0.10	0.15
L	19.80	19.92	20.10
L1	-	-	4.30
ΦP	3.50	3.60	3.70
ΦP1	-	-	7.30
ΦP2	2.40	2.50	2.60
Q	5.60	5.80	6.00
S		6.15BSC	
R		0.50REF	
T	9.80	-	10.20
T1		1.65REF	
T2		8.00REF	
T3		12.80REF	
U	6.00	-	6.40
θ1	6°	7°	8°
θ2	4°	5°	6°
θ3	1°	-	1.5°
θ4	14°	15°	16°

Package Outline

TO-3P



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.60	4.80	5.00
A1	1.40	1.50	1.60
A2	1.33	1.38	1.43
b	0.80	1.00	1.20
b1	2.80	3.00	3.20
b2	1.80	2.00	2.20
c	0.50	0.60	0.70
D	19.75	19.90	20.05
D1	13.70	13.90	14.10
D2	12.90REF		
E	15.40	15.60	15.80
E1	13.40	13.60	13.80
E2	9.40	9.60	9.80
e	5.45 TYP		
G	4.60	4.80	5.00
H	40.30	40.50	40.70
H1	23.20	23.40	23.60
h	0.05	0.10	0.15
L	7.40 TYP		
L1	9.00 TYP		
L2	11.00 TYP		
L3	1.00 REF		
ΦP	6.90	7.00	7.10
ΦP1	3.20 REF		
ΦP2	3.50 REF		
ΦP3	1.40	1.50	1.60
R	0.50 REF		
Q	5.00 REF		
Q1	12.56	12.76	12.96
U	7.8	8	8.2
θ1	5°	7°	9°
θ2	1°	3°	5°
θ3	60° REF		

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